PDTC123J series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

Rev. 7 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			PNP	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTC123JE	SOT416	SC-75	-	PDTA123JE	ultra small	
PDTC123JM	SOT883	SC-101	-	PDTA123JM	leadless ultra small	
PDTC123JT	SOT23	-	TO-236AB	PDTA123JT	small	
PDTC123JU	SOT323	SC-70	-	PDTA123JU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

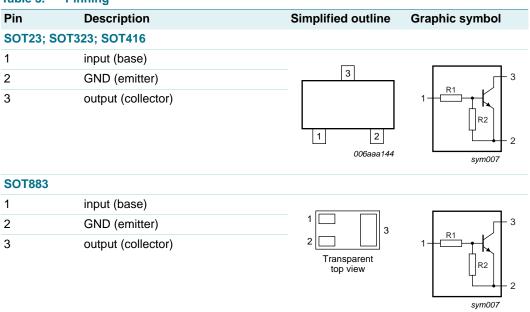
Table 2. Quick reference data

V _{CEO} collector-emi	tter voltage	open base	_	_	Ε0	
				-	50	V
I _O output currer	nt		-	-	100	mA
R1 bias resistor	1 (input)		1.54	2.20	2.86	kΩ
R2/R1 bias resistor	ratio		17	21	26	



2. Pinning information

Table 3. Pinning



3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTC123JE	SC-75	plastic surface-mounted package; 3 leads	SOT416			
PDTC123JM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTC123JT	-	plastic surface-mounted package; 3 leads	SOT23			
PDTC123JU	SC-70	plastic surface-mounted package; 3 leads	SOT323			

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTC123JE	28
PDTC123JM	DW
PDTC123JT	*25
PDTC123JU	*49

^{[1] * =} placeholder for manufacturing site code.

5. Limiting values

Table 6. Limiting values

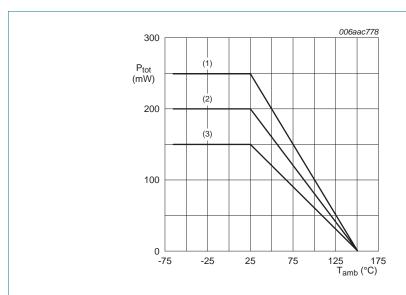
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
V_{I}	input voltage				
	positive		-	+12	V
	negative		-	-5	V
Io	output current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1$ ms	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTC123JE (SOT416)		[1][2]	150	mW
	PDTC123JM (SOT883)		[2][3]	250	mW
	PDTC123JT (SOT23)		<u>[1]</u> -	250	mW
	PDTC123JU (SOT323)		<u>[1]</u> -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

 $[\]begin{tabular}{ll} [2] & Reflow soldering is the only recommended soldering method. \end{tabular}$

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTC123JE (SOT416)		[1][2]	-	830	K/W
	PDTC123JM (SOT883)		[2][3]	-	500	K/W
	PDTC123JT (SOT23)		[1] -	-	500	K/W
	PDTC123JU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.

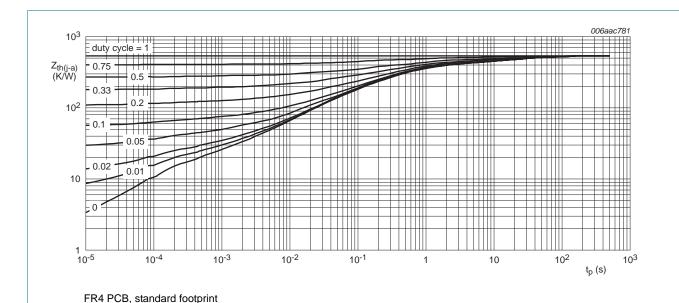
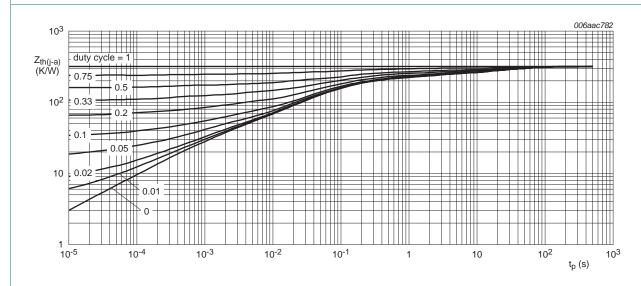
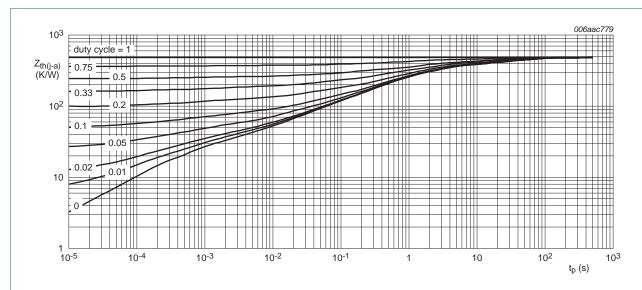


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC123JE (SOT416); typical values



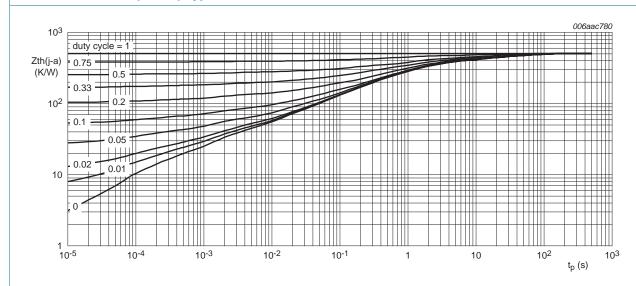
FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC123JM (SOT883); typical values



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC123JT (SOT23); typical values



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC123JU (SOT323); typical values

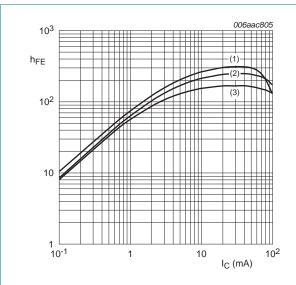
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	180	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	100	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	0.6	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V; } I_{C} = 5 \text{ mA}$	1.1	0.75	-	V
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	[1] -	230	-	MHz

^[1] Characteristics of built-in transistor.



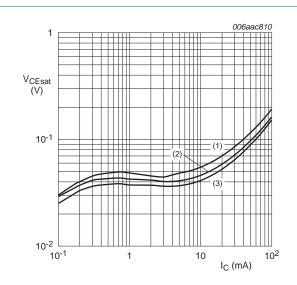
$$V_{CE} = 5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



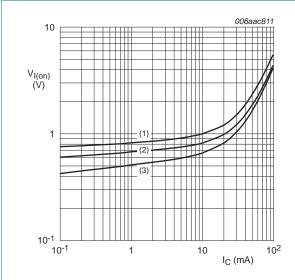
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



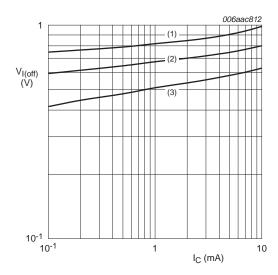
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) T_{amb} = 100 °C

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Off-state input voltage as a function of collector current; typical values

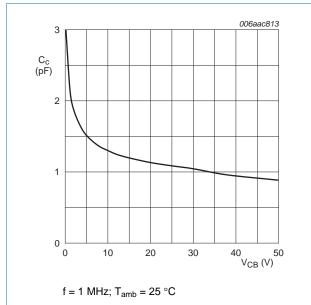


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

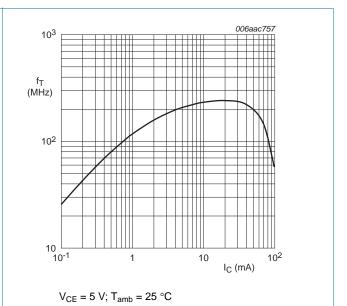


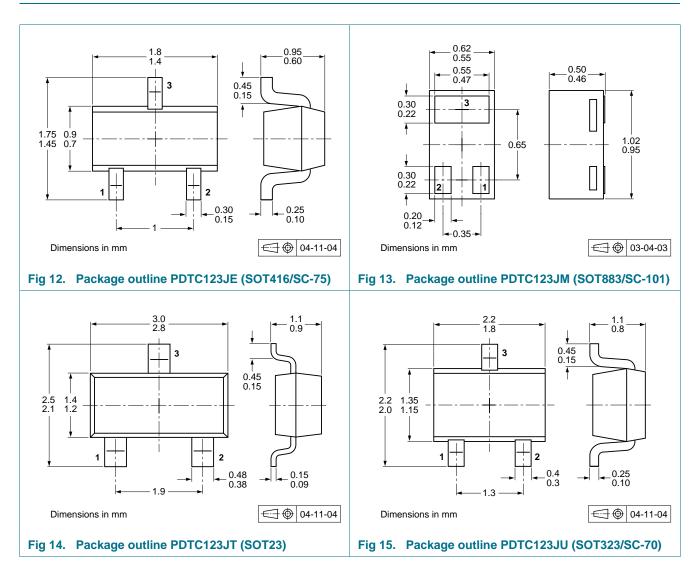
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity		
			3000	10000		
PDTC123JE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135		
PDTC123JM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315		
PDTC123JT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
PDTC123JU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135		

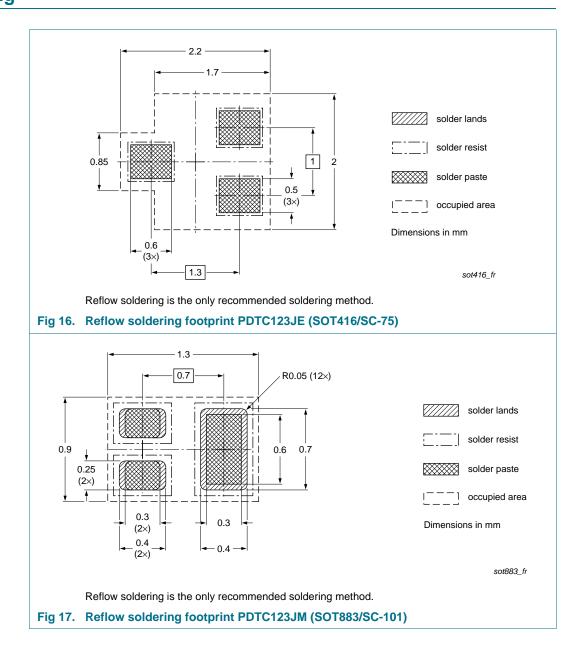
^[1] For further information and the availability of packing methods, see $\underline{\text{Section 14}}$.

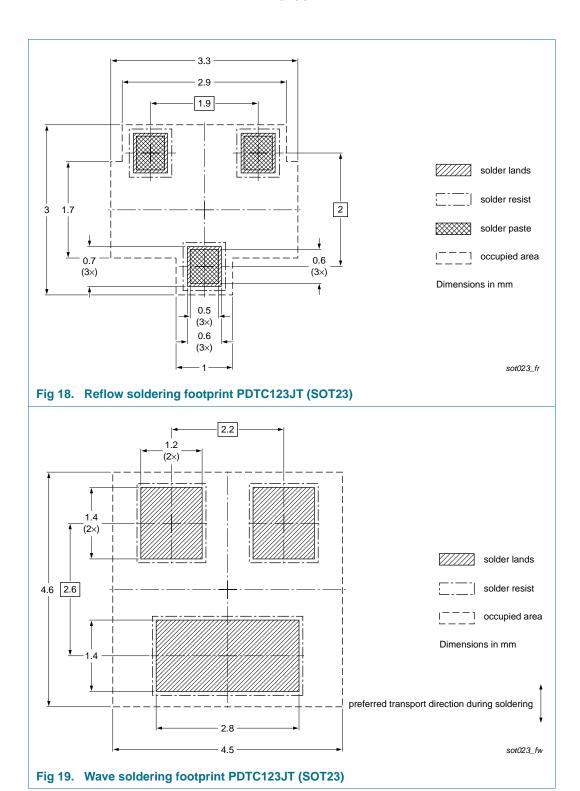
PDTC123J_SER

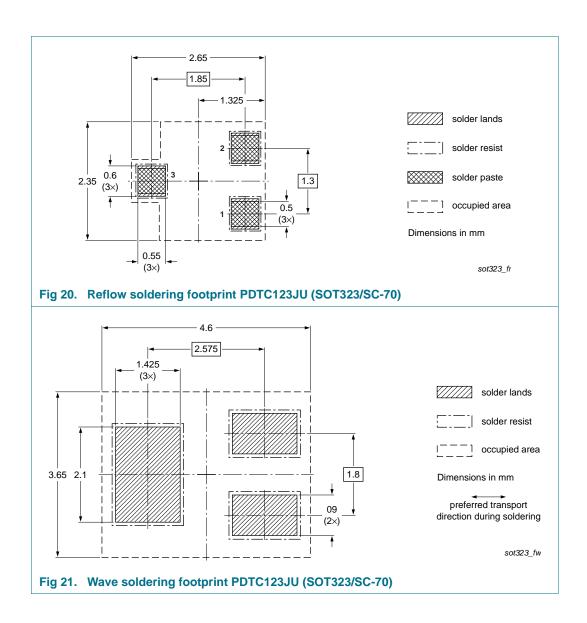
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11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC123J_SER v.7	20111221	Product data sheet	-	PDTC123J_SER v.6
Modifications:	• Figure 3 and	d <u>5</u> : corrected		
PDTC123J_SER v.6	20111215	Product data sheet	-	PDTC123J_SERIES v.5
PDTC123J_SERIES v.5	20040813	Product data sheet	-	PDTC123J_SERIES v.4
PDTC123J_SERIES v.4	20030410	Product specification	-	-

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13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PDTC123J SER

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PDTC123J series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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PDTC123J series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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